R1LV3216R Series

32Mb Advanced LPSRAM (2M word x 16bit / 4M word x 8bit)

REJ03C0367-0100
Rev.1.00
2009.05.07

Description

The R1LV3216R Series is a family of low voltage 32-Mbit static RAMs organized as 2,097,152-word by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1LV3216R Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1LV3216R Series is provided in 48-pin thin small outline package [TSOP (I): 12mm x 20mm with pin pitch of 0.5mm] and 52-pin micro thin small outline package [µTSOP (II): 10.79mm x 10.49mm with pin pitch of 0.4mm]. It gives the best solution for compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

Features

- Single 2.7~3.6V power supply
- Small stand-by current: 4 µA (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

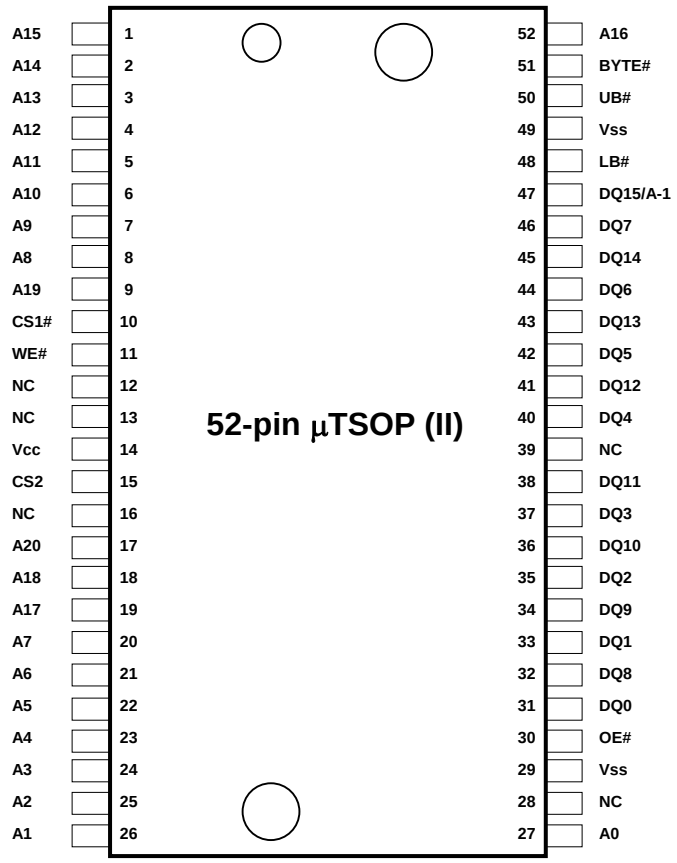
Ordering Information

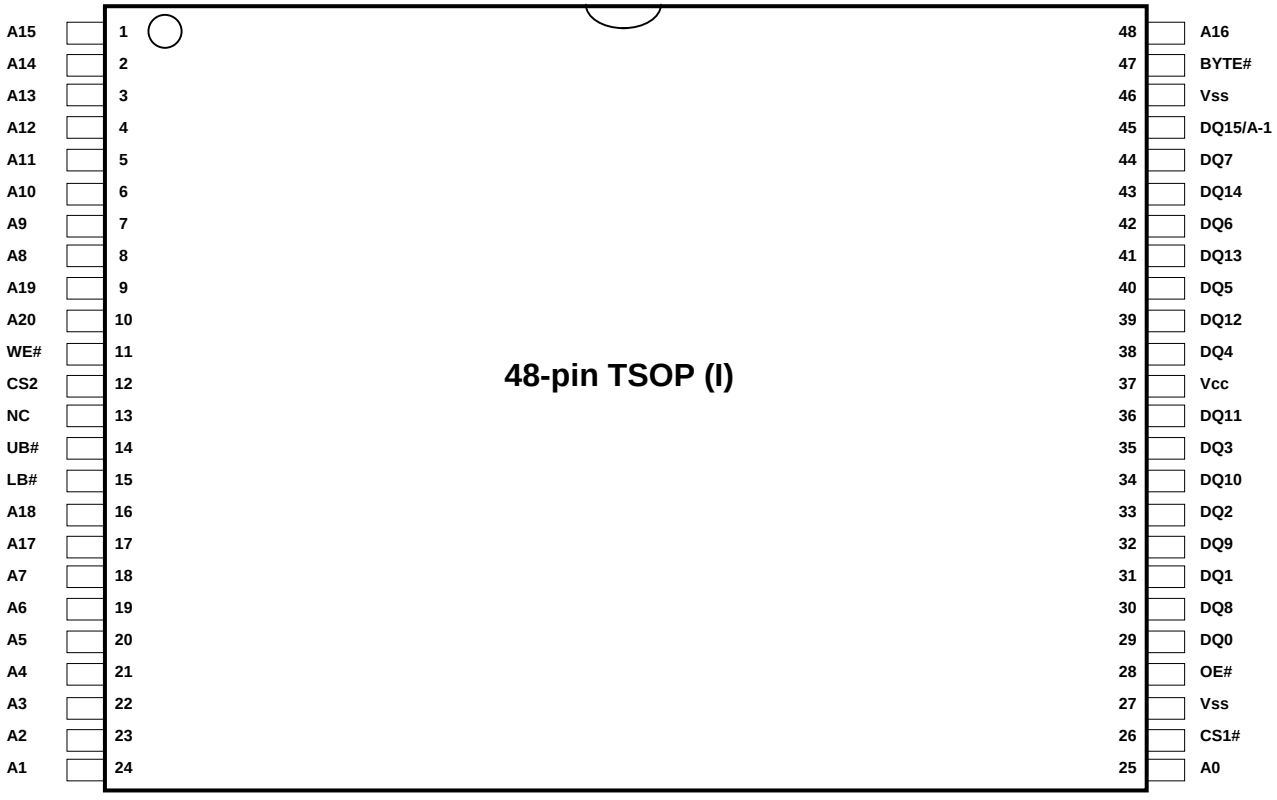
Type No.	Access time	Package
R1LV3216RSA-5S%	55 ns	12mm x 20mm 48-pin plastic TSOP (I) (normal-bend type) (48P3R)
R1LV3216RSA-7S%	70 ns	
R1LV3216RSD-5S%	55 ns	350 mil 52-pin plastic µ-TSOP (II) (normal-bend type) (52PTG)
R1LV3216RSD-7S%	70 ns	

% - Temperature version; see table below

%	Temperature Range
R	0 ~ +70 °C
I	-40 ~ +85 °C

Pin Arrangement

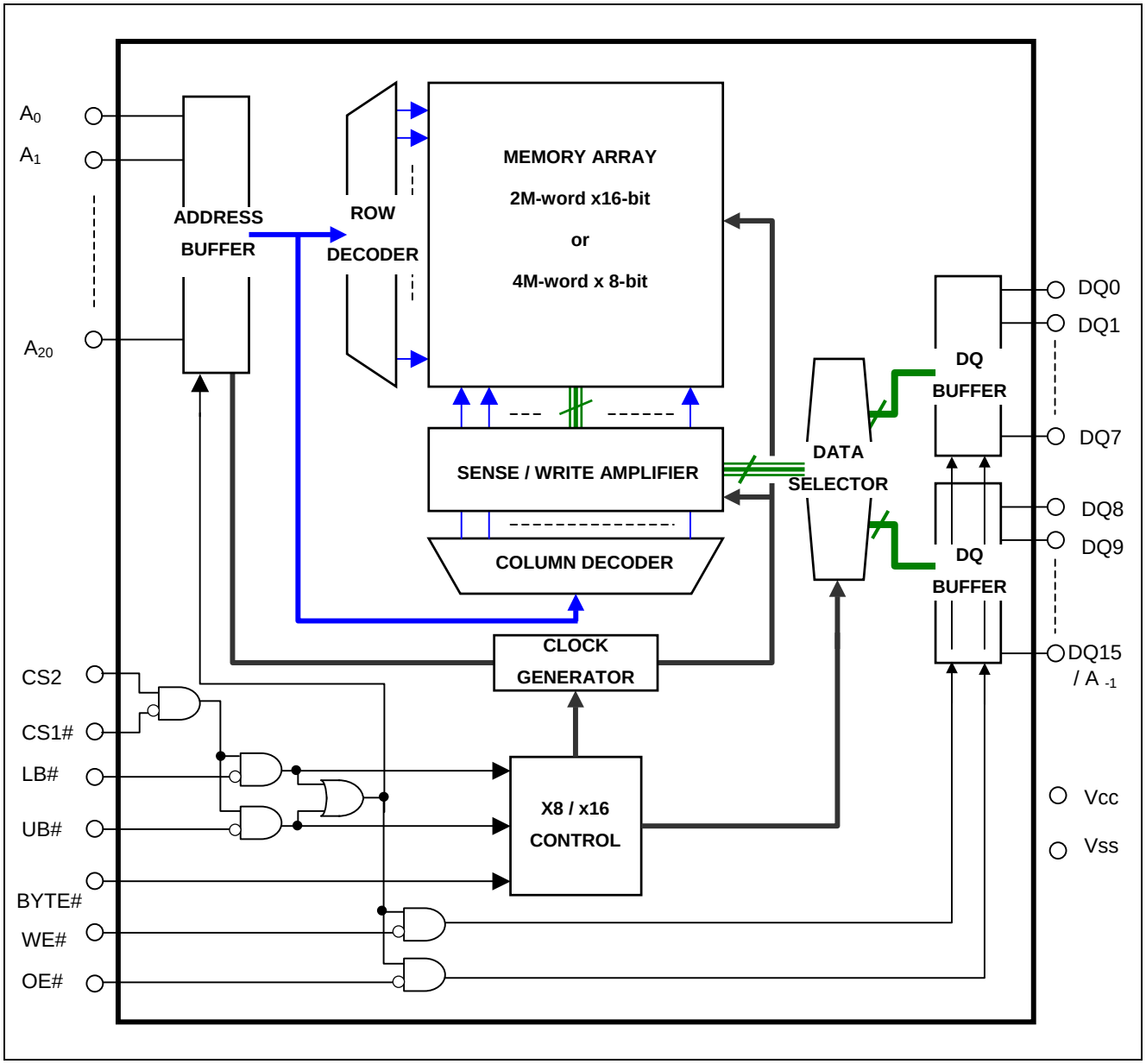




Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A20	Address input (word mode)
A-1 to A20	Address input (byte mode)
DQ0 to DQ15	Data input/output
CS1#	Chip select 1
CS2	Chip select 2
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable
BYTE#	Byte control mode enable
NC	Non connection

Block Diagram



Operation Table

CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0~7	DQ8~14	DQ15	Operation
H	X	X	X	X	X	X	High-Z	High-Z	High-Z	Stand-by
X	L	X	X	X	X	X	High-Z	High-Z	High-Z	Stand-by
X	X	H	H	H	X	X	High-Z	High-Z	High-Z	Stand-by
L	H	H	L	H	L	X	Din	High-Z	High-Z	Write in lower byte
L	H	H	L	H	H	L	Dout	High-Z	High-Z	Read in lower byte
L	H	H	L	H	H	H	High-Z	High-Z	High-Z	Output disable
L	H	H	H	L	L	X	High-Z	Din	Din	Write in upper byte
L	H	H	H	L	H	L	High-Z	Dout	Dout	Read in upper byte
L	H	H	H	L	H	H	High-Z	High-Z	High-Z	Output disable
L	H	H	L	L	L	X	Din	Din	Din	Word write
L	H	H	L	L	H	L	Dout	Dout	Dout	Word read
L	H	H	L	L	H	H	High-Z	High-Z	High-Z	Output disable
L	H	L	L	L	L	X	Din	High-Z	A-1	Byte write
L	H	L	L	L	H	L	Dout	High-Z	A-1	Byte read
L	H	L	L	L	H	H	High-Z	High-Z	A-1	Output disable

Note 1. H: V_{IH} L:V_{IL} X: V_{IH} or V_{IL}

2. When apply BYTE# ="L", please assign LB#=UB#="L".

Absolute Maximum Ratings

Parameter	Symbol	Value		unit
Power supply voltage relative to Vss	Vcc	-0.5 to +4.6		V
Terminal voltage on any pin relative to Vss	V_T	-0.5[*1] to Vcc+0.3[*2]		V
Power dissipation	P_T	0.7		W
Operation temperature	Topr[*3]	R ver.	0 to +70	°C
		I ver.	-40 to +85	°C
Storage temperature range	Tstg	-65 to 150		°C
Storage temperature range under bias	Tbias[*3]	R ver.	0 to +70	°C
		I ver.	-40 to +85	°C

Note 1. –2.0V in case of AC (Pulse width ≤30ns)

2. Maximum voltage is +4.6V.

3. Ambient temperature range depends on R/I-version. Please see table on page 1.

Recommended Operating Conditions

Parameter		Symbol	Min.	Typ.	Max.	Unit	Note
Supply voltage		Vcc	2.7	3.0	3.6	V	
		Vss	0	0	0	V	
Input high voltage		V_{IH}	2.4	-	Vcc+0.2	V	
Input low voltage		V_{IL}	-0.2	-	0.4	V	1
Ambient temperature range	R ver.	Ta	0	-	+70	°C	2
	I ver.		-40	-	+85	°C	2

Note 1. –2.0V in case of AC (Pulse width ≤ 30ns)
2. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Input leakage current	$\lvert I_{LI} \rvert$	-	-	1	µA	Vin = Vss to Vcc	
Output leakage current	$\lvert I_{LO} \rvert$	-	-	1	µA	BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V CS1# =V_{IH} or CS2 =V_{IL} or OE# =V_{IH} or WE# =V_{IL} or LB# = UB# =V_{IH}, VI/O =Vss to Vcc	
Average operating current	I_{CC1}	-	40[*1]	55	mA	Min. cycle, duty =100%, II/O = 0mA BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V CS1# =V_{IL}, CS2 =V_{IH}, Others = V_{IH}/V_{IL}	
	I_{CC2}	-	3[*1]	8	mA	Cycle =1µs, duty =100%, II/O = 0mA BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V CS1# ≤ 0.2V, CS2 ≥ V_{CC}-0.2V, V_{IH} ≥ V_{CC}-0.2V, V_{IL} ≤ 0.2V	
Standby current	I_{SB}	-	0.1[*1]	0.3	mA	BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V CS2 =V_{IL}	
Standby current	I_{SB1}	-	4[*1]	12	µA	~+25°C	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V_{CC}-0.2V, CS2 ≥ V_{CC}-0.2V or (3) LB# = UB# ≥ V_{CC}-0.2V, CS1# ≤ 0.2V, CS2 ≥ V_{CC}-0.2V
		-	7[*2]	24	µA	~+40°C	
		-	-	50	µA	~+70°C	
		-	-	80	µA	~+85°C	
Output high voltage	V_{OH}	2.4	-	-	V	BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V I_{OH} = -0.5mA	
Output low voltage	V_{OL}	-	-	0.4	V	BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V I_{OL} = 2mA	

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25ºC), and not 100% tested.
2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 40ºC), and not 100% tested.

Capacitance

(Ta =25°C, f =1MHz)

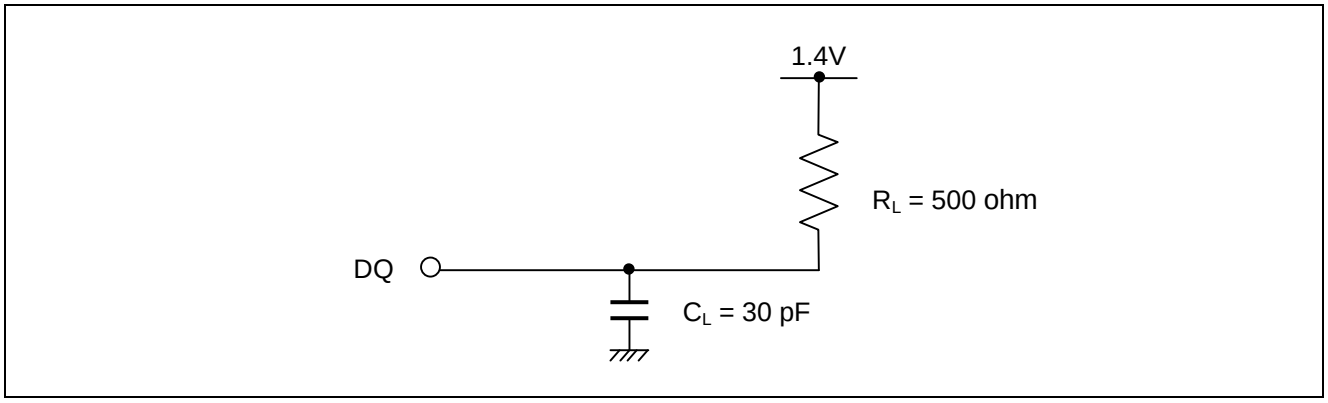
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	10	pF	Vin =0V	1
Input / output capacitance	$C_{I/O}$	-	-	10	pF	$V_{I/O}$ =0V	1

Note1.This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (Vcc = 2.7V ~ 3.6V, Ta = 0 ~ +70°C / -40 ~ +85°C[*1])

- Input pulse levels: V_{IL} = 0.4V, V_{IH} = 2.4V
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Note1. Ambient temperature range depends on R/I-version. Please see table on page 1.

Read Cycle

Parameter	Symbol	R1LV3216R**-5S		R1LV3216R**-7S		Unit	Note
		Min.	Max.	Min.	Max.		
Read cycle time	t_{RC}	55	-	70	-	ns	
Address access time	t_{AA}	-	55	-	70	ns	
Chip select access time	t_{ACS1}	-	55	-	70	ns	
	t_{ACS2}	-	55	-	70	ns	
Output enable to output valid	t_{OE}	-	25	-	35	ns	
Output hold from address change	t_{OH}	10	-	10	-	ns	
LB#, UB# access time	t_{BA}	-	55	-	70	ns	
Chip select to output in low-Z	t_{CLZ1}	10	-	10	-	ns	2,3
	t_{CLZ2}	10	-	10	-	ns	2,3
LB#, UB# enable to low-Z	t_{BLZ}	5	-	5	-	ns	2,3
Output enable to output in low-Z	t_{OLZ}	5	-	5	-	ns	2,3
Chip deselect to output in high-Z	t_{CHZ1}	0	20	0	25	ns	1,2,3
	t_{CHZ2}	0	20	0	25	ns	1,2,3
LB#, UB# disable to high-Z	t_{BHZ}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2,3

Write Cycle

Parameter	Symbol	R1LV3216R**-5S		R1LV3216R**-7S		Unit	Note
		Min.	Max.	Min.	Max.		
Write cycle time	t_{WC}	55	-	70	-	ns	
Address valid to end of write	t_{AW}	50	-	65	-	ns	
Chip select to end of write	t_{CW}	50	-	65	-	ns	5
Write pulse width	t_{WP}	40	-	55	-	ns	4
LB#, UB# valid to end of write	t_{BW}	50	-	65	-	ns	
Address setup time	t_{AS}	0	-	0	-	ns	6
Write recovery time	t_{WR}	0	-	0	-	ns	7
Data to write time overlap	t_{DW}	25	-	35	-	ns	
Data hold from write time	t_{DH}	0	-	0	-	ns	
Output enable from end of write	t_{OW}	5	-	5	-	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2
Write to output in high-Z	t_{WHZ}	0	20	0	25	ns	1,2

Note1. t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

2. This parameter is sampled and not 100% tested.

3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.

4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.
A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low .
A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. t_{WP} is measured from the beginning of write to the end of write.

5. t_{CW} is measured from the later of CS1# going low or CS2 going high to end of write.

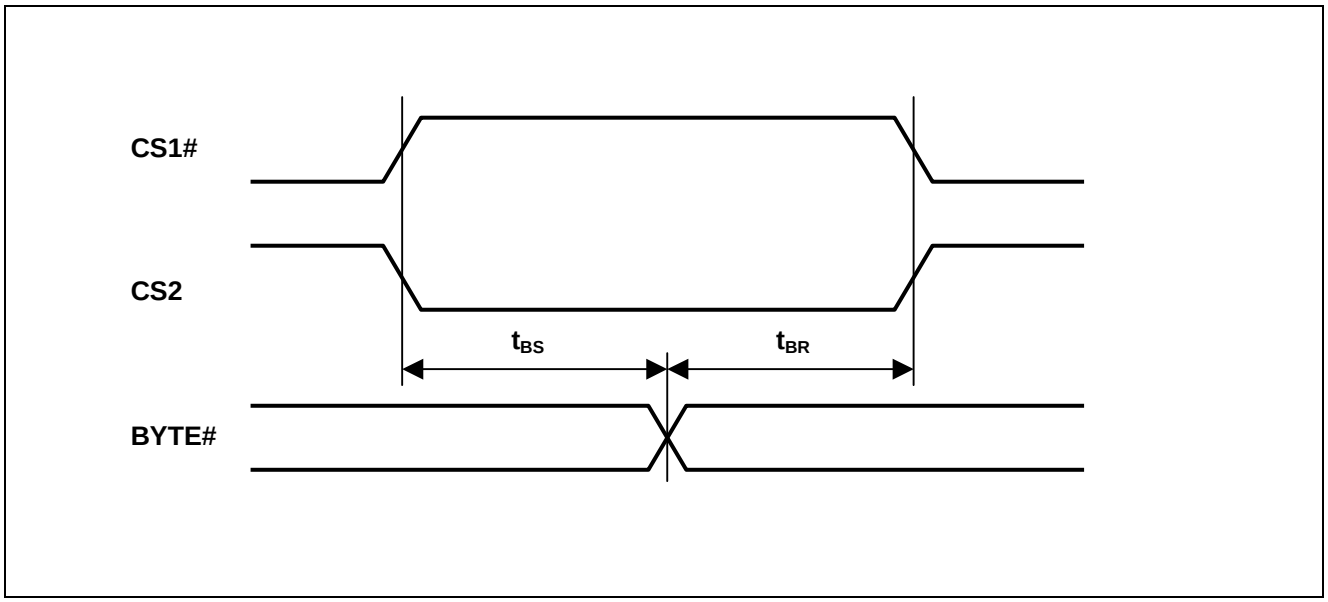
6. t_{AS} is measured the address valid to the beginning of write.

7. t_{WR} is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

BYTE# Timing Conditions

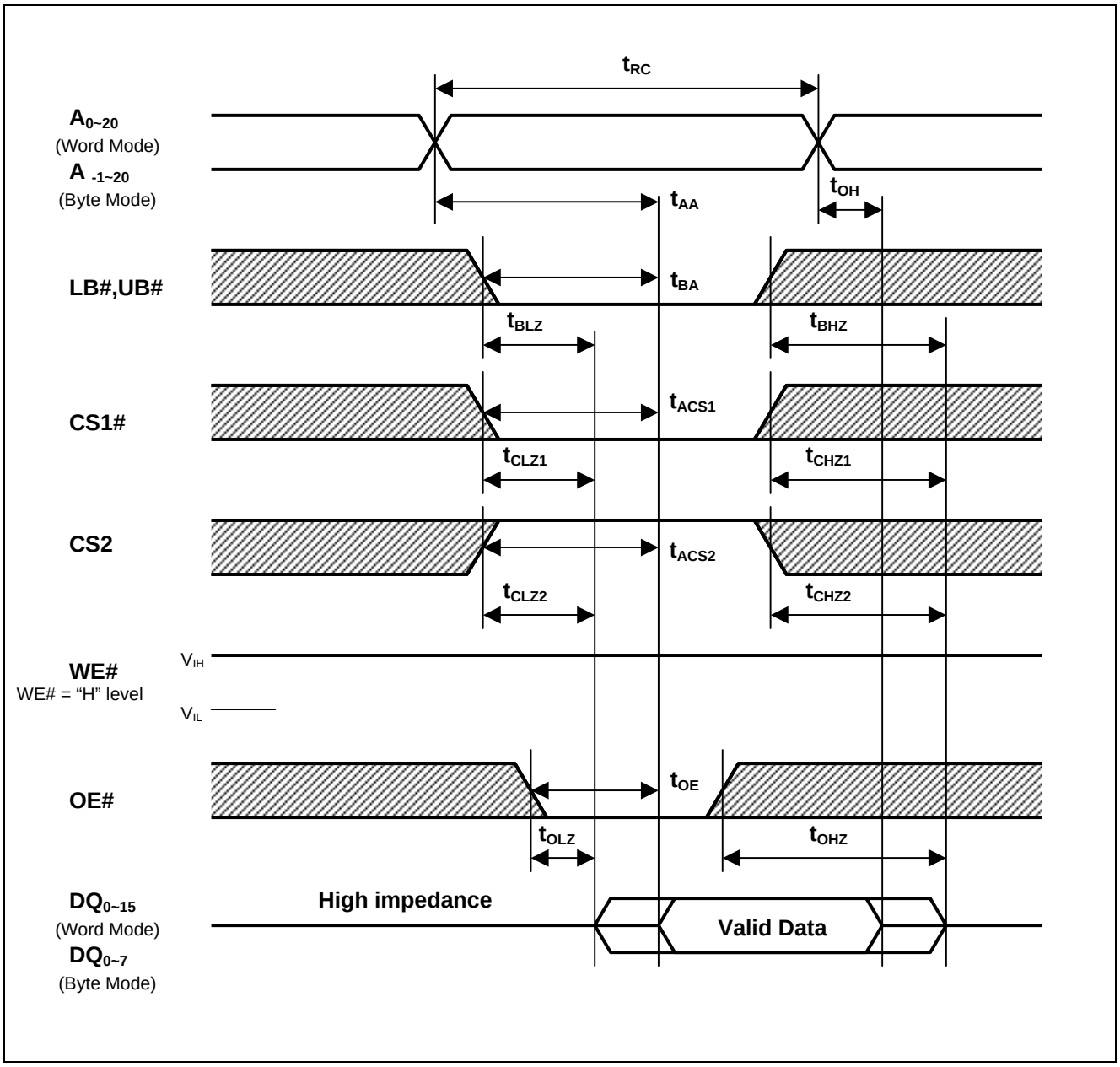
Parameter	Symbol	R1LV3216R**-5S		R1LV3216R**-7S		Unit	Note
		Min.	Max.	Min.	Max.		
Byte setup time	t_{BS}	5	-	5	-	ms	
Byte recovery time	t_{BR}	5	-	5	-	ms	

BYTE# Timing Waveforms



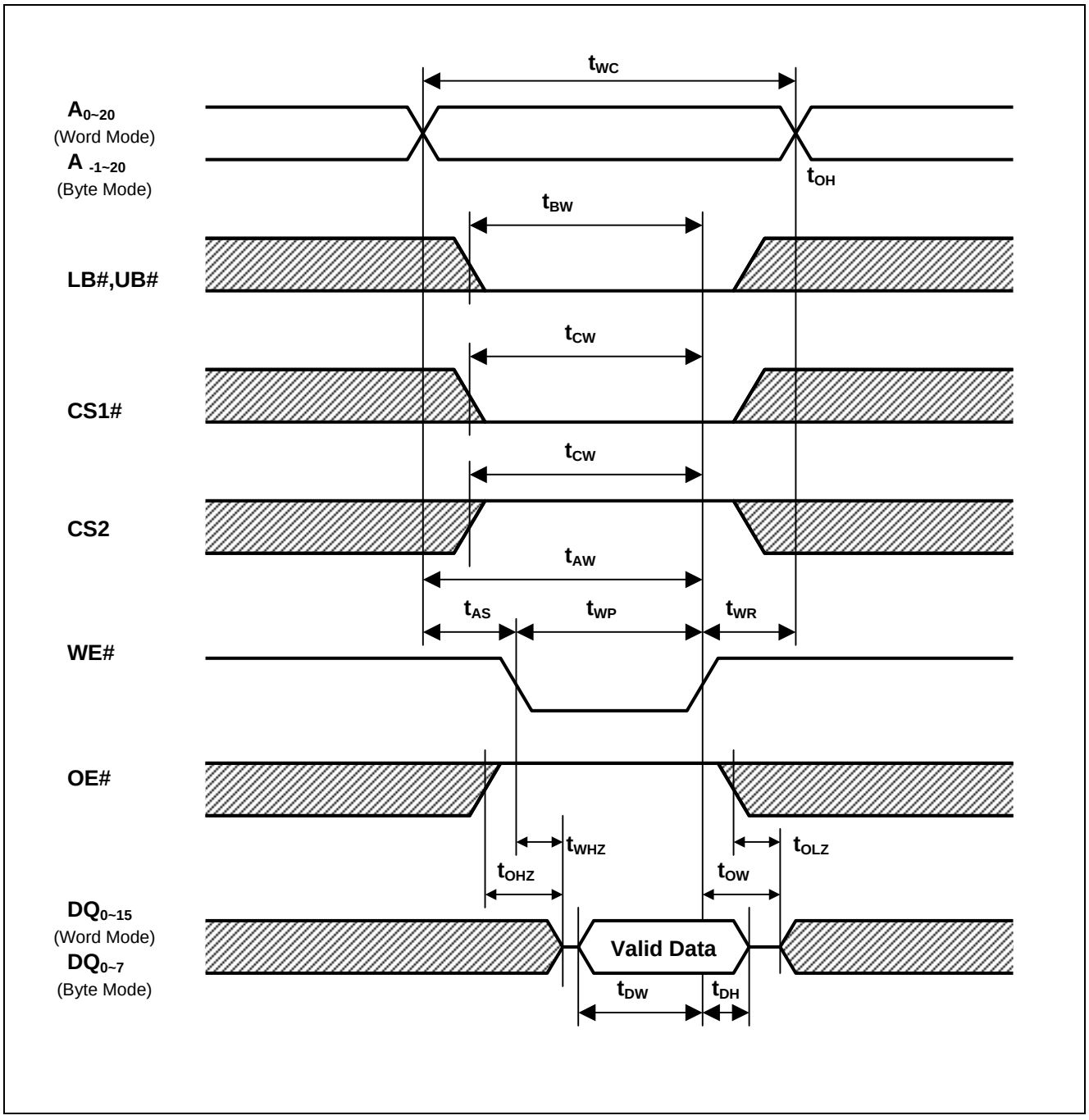
Timing Waveforms

Read Cycle[*1]



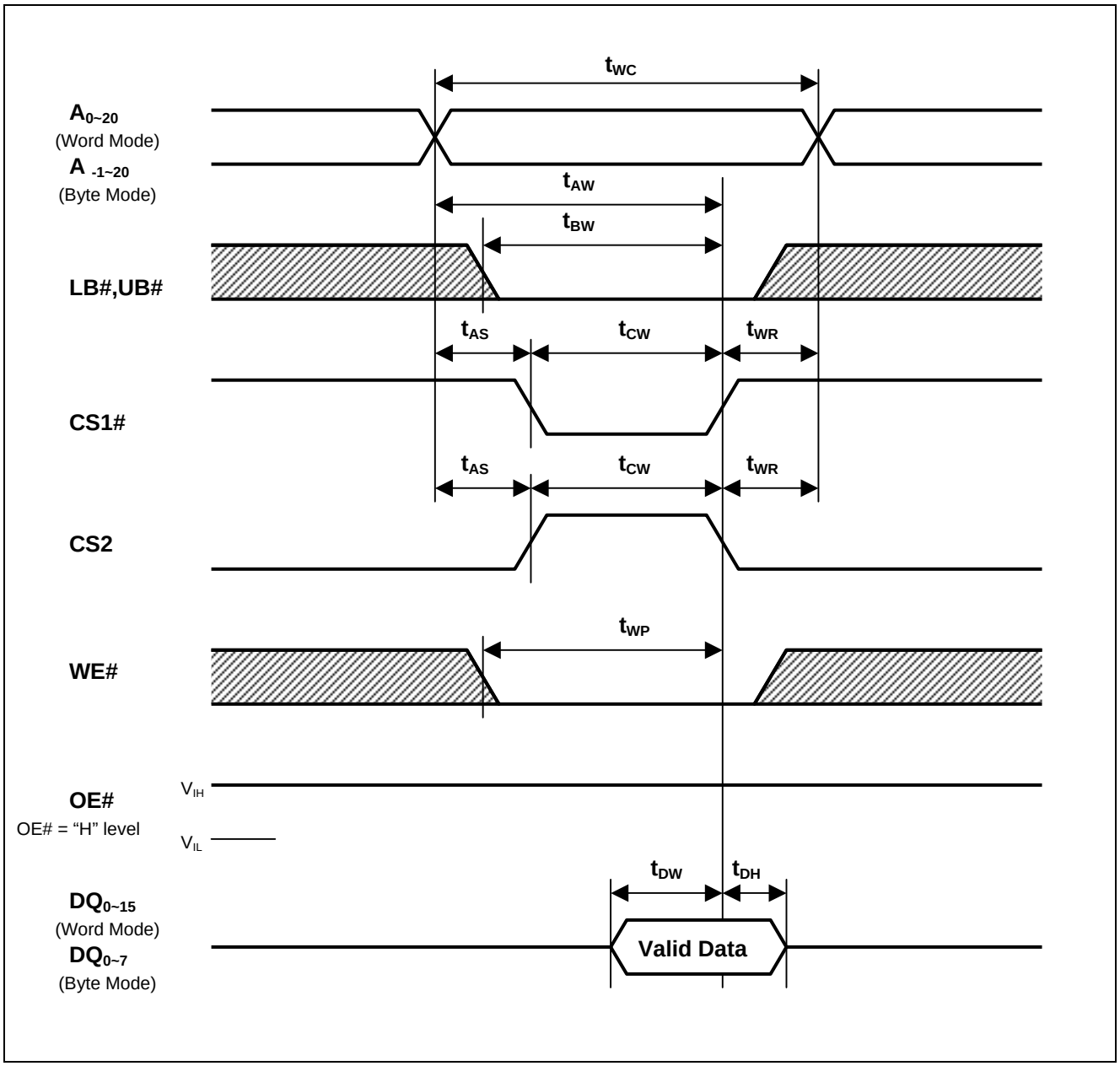
Note1. BYTE# ≥ Vcc – 0.2V or BYTE# ≤ 0.2V

Write Cycle (1)[*1] (WE# CLOCK)



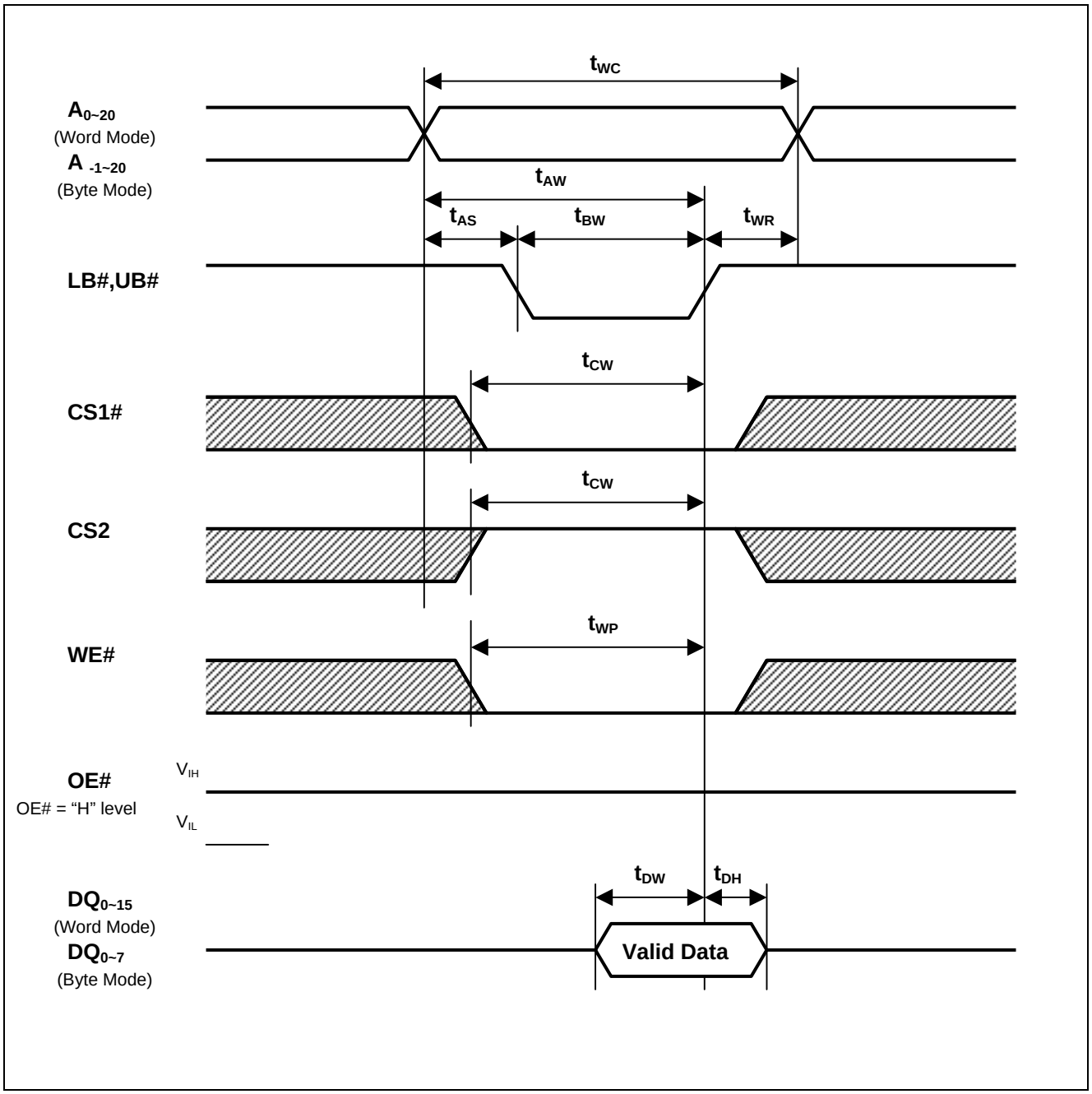
Note1. BYTE# ≥ Vcc – 0.2V or BYTE# ≤ 0.2V

Write Cycle (2)[*1] (CS1#, CS2 CLOCK)



Note1. BYTE# ≥ Vcc – 0.2V or BYTE# ≤ 0.2V

Write Cycle (3)[*1] (LB#, UB# CLOCK)



Note1. BYTE# ≥ Vcc – 0.2V or BYTE# ≤ 0.2V

Low Vcc Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions[*3]	
V_{CC} for data retention	V_{DR}	2.0	-	3.6	V	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V_{CC}-0.2V, CS2 ≥ V_{CC}-0.2V or (3) LB# = UB# ≥ V_{CC}-0.2V, CS1# ≤ 0.2V, CS2 ≥ V_{CC}-0.2V	
Data retention current	I_{CCDR}	-	4[*1]	12	µA	~+25°C	Vin ≥ 0V BYTE# ≥ Vcc -0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V_{CC}-0.2V, CS2 ≥ V_{CC}-0.2V or (3) LB# = UB# ≥ V_{CC}-0.2V, CS1# ≤ 0.2V, CS2 ≥ V_{CC}-0.2V
		-	7[*2]	24	µA	~+40°C	
		-	-	50	µA	~+70°C	
		-	-	80	µA	~+85°C	
Chip select to data retention time	t_{CDR}	0	-	-	ns	See retention waveform.	
Operation recovery time	t_R	5	-	-	ms		

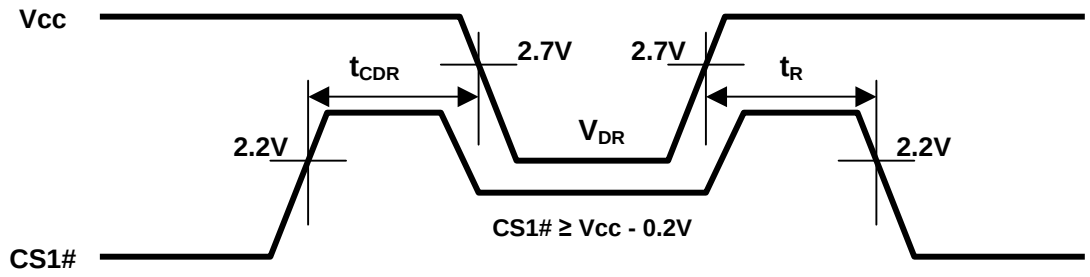
Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25ºC), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 40ºC), and not 100% tested.

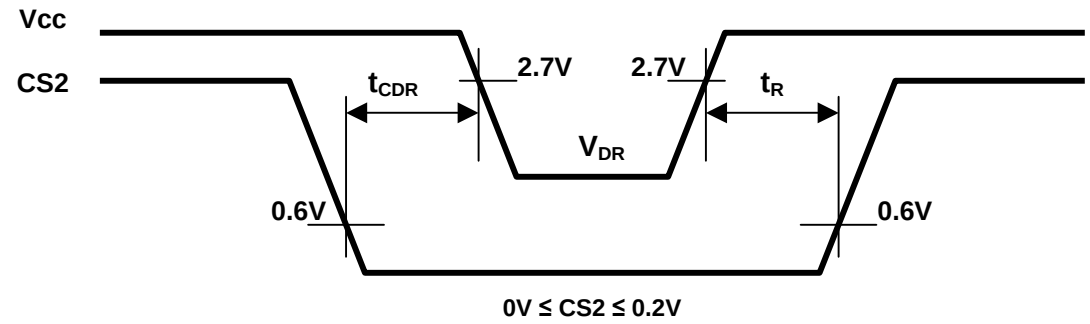
3. CS2 also controls address buffer, WE# buffer ,CS1# buffer ,OE# buffer ,LB# ,UB# buffer and Din buffer. If CS2 controls data retention mode, Vin levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ Vcc-0.2V or0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms[*1]

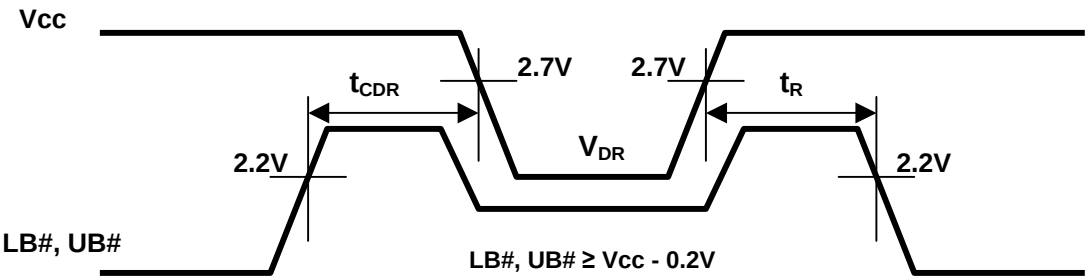
(1) CS1# Controlled



(2) CS2 Controlled



(3) LB#, UB Controlled



Note1. BYTE# ≥ Vcc – 0.2V or BYTE# ≤ 0.2V

Revision History	R1LV3216R Series Data Sheet

Rev.	Date	Contents of Revision	
		Page	Description
0.01	Mar.24, 2008	-	Initial issue: Preliminary Data Sheet
1.00	May 07, 2009	-	Finalized
		5	Operation Table corrected
		6	Error corrected: I_{SB} Test condition CS2=V_{IH}->V_{IL}

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